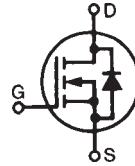


Polar™ Power MOSFET HiPerFET™

IXFH10N100P
IXFV10N100P
IXFV10N100PS

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode

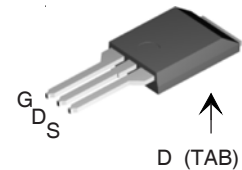


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	1000	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C , $R_{GS} = 1\text{M}\Omega$	1000	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ\text{C}$	10	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	25	A
I_A	$T_C = 25^\circ\text{C}$	5	A
E_{AS}	$T_C = 25^\circ\text{C}$	500	mJ
dV/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$	15	V/ns
P_D	$T_C = 25^\circ\text{C}$	380	W
T_J		$-55 \dots +150$	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		$-55 \dots +150$	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering	300	$^\circ\text{C}$
T_{SOLD}	Plastic body for 10s	260	$^\circ\text{C}$
M_d	Mounting torque (TO-247)	1.13/10	Nm/lb.in.
F_C	Mounting force (PLUS220)	11..65/2.5..14.6	N/lb.
Weight	TO-247	6	g
	PLUS 220 types	4	g

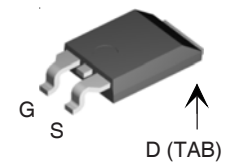
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0\text{V}$, $I_D = 1\text{mA}$	1000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 1\text{mA}$	3.5		6.5 V
I_{GSS}	$V_{GS} = \pm 30\text{V}$, $V_{DS} = 0\text{V}$			± 100 nA
I_{DSS}	$V_{DS} = V_{DSS}$			25 μA
	$V_{GS} = 0\text{V}$ $T_J = 125^\circ\text{C}$			1.25 mA
$R_{DS(on)}$	$V_{GS} = 10\text{V}$, $I_D = 0.5 \cdot I_{D25}$, Note 1			1.4 Ω

$$\begin{aligned}
 V_{DSS} &= 1000\text{V} \\
 I_{D25} &= 10\text{A} \\
 R_{DS(on)} &\leq 1.4\Omega \\
 t_{rr} &\leq 300\text{ns}
 \end{aligned}$$

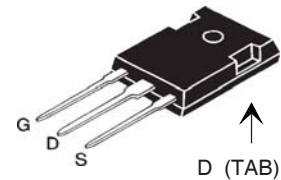
PLUS220 (IXFV)



PLUS220SMD (IXFV_S)



TO-247 (IXFH)



G = Gate D = Drain
S = Source TAB = Drain

Features

- International standard packages
- Fast recovery diode
- Avalanche rated
- Low package inductance

Advantages

- Easy to mount
- Space savings
- High power density

Applications:

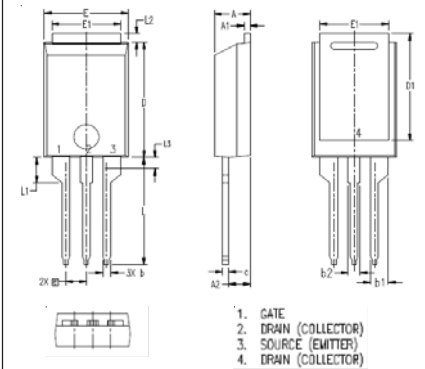
- Switched-mode and resonant-mode power supplies
- DC-DC Converters
- Laser Drivers
- AC and DC motor drives
- Robotics and servo controls

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 20\text{V}, I_D = 0.5 \cdot I_{D25}$, Note 1	4.2	6.5	S
C_{iss}	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		3030	pF
C_{oss}			200	pF
C_{rss}			34	pF
R_{Gi}	Gate input resistance		1.8	Ω
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 3.3\Omega$ (External)		38	ns
t_r			45	ns
$t_{d(off)}$			47	ns
t_f			75	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		56	nC
Q_{gs}			19	nC
Q_{gd}			30	nC
R_{thJC}	(TO-247 & PLUS220)			0.33 $^\circ\text{C/W}$
R_{thCS}			0.21	$^\circ\text{C/W}$

Source-Drain Diode		Characteristic Values		
$T_J = 25^\circ\text{C}$ unless otherwise specified)		Min.	Typ.	Max.
I_s	$V_{GS} = 0\text{V}$			10 A
I_{SM}	Repetitive, pulse width limited by T_{JM}			40 A
V_{SD}	$I_F = I_s, V_{GS} = 0\text{V}$, Note 1			1.5 V
t_{rr}	$I_F = 5\text{A}, -di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}, V_{GS} = 0\text{V}$			300 ns
I_{RM}			7.3	A

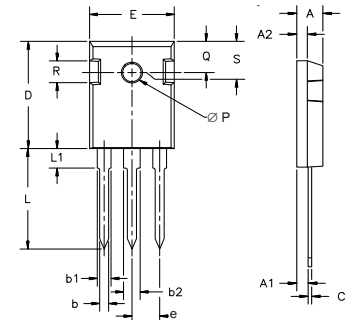
Note 1: Pulse test, $t \leq 300\mu\text{s}$; duty cycle, $d \leq 2\%$.

PLUS220 (IXFV) Outline



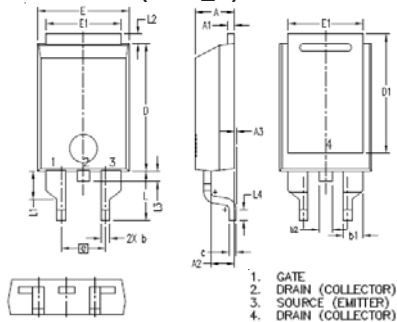
SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.169	.185	4.30	4.70
A1	.028	.035	0.70	0.90
A2	.098	.118	2.50	3.00
b	.035	.047	0.90	1.20
b1	.080	.095	2.03	2.41
b2	.054	.064	1.37	1.63
c	.028	.035	0.70	0.90
D	.551	.591	14.00	15.00
D1	.512	.539	13.00	13.70
E	.394	.433	10.00	11.00
E1	.331	.346	8.40	8.80
e	.100 BSC		2.54 BSC	
L	.512	.551	13.00	14.00
L1	.118	.138	3.00	3.50
L2	.035	.051	0.90	1.30
L3	.047	.059	1.20	1.50

TO-247 (IXFH) Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A1	2.2	2.54	.087	.102
A2	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b1	1.65	2.13	.065	.084
b2	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

PLUS220SMD (IXFV_S) Outline



SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.169	.185	4.30	4.70
A1	.028	.035	0.70	0.90
A2	.098	.118	2.50	3.00
A3	.000	.010	0.00	0.25
b	.035	.047	0.90	1.20
b1	.080	.095	2.03	2.41
b2	.054	.064	1.37	1.63
c	.028	.035	0.70	0.90
D	.551	.591	14.00	15.00
D1	.512	.539	13.00	13.70
E	.394	.433	10.00	11.00
E1	.331	.346	8.40	8.80
e	.200 BSC		5.08 BSC	
L	.209	.228	5.30	5.80
L1	.118	.138	3.00	3.50
L2	.035	.051	0.90	1.30
L3	.047	.059	1.20	1.50
L4	.039	.059	1.00	1.50

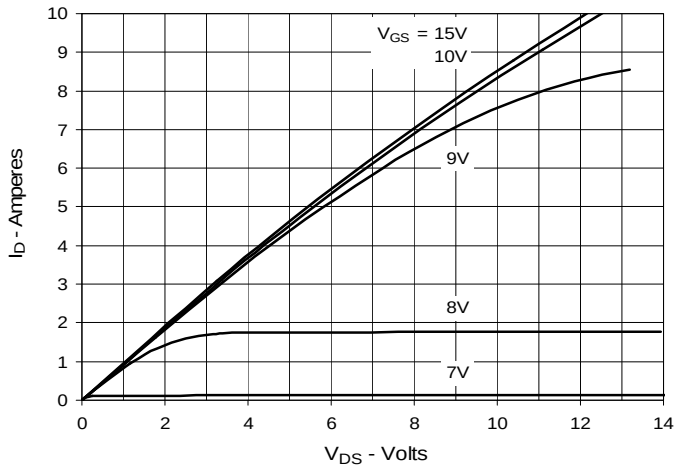
PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

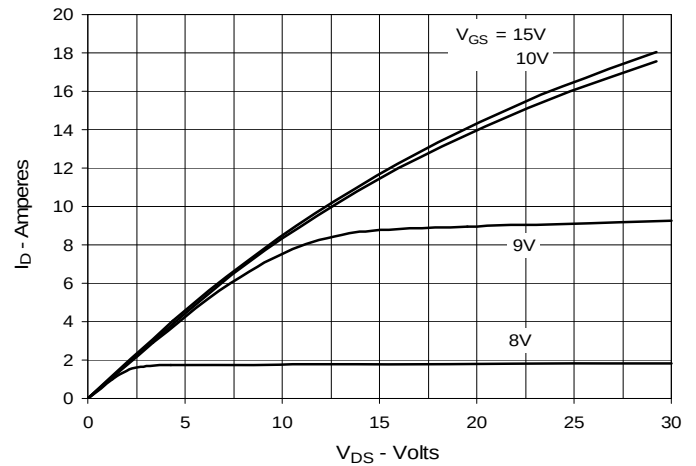
IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

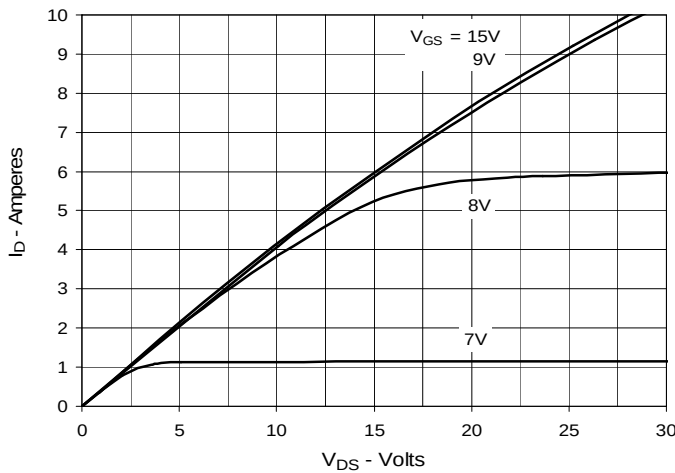
**Fig. 1. Output Characteristics
@ 25°C**



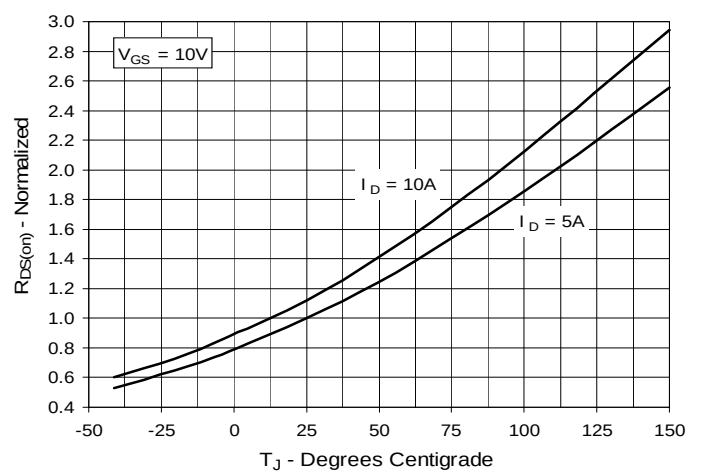
**Fig. 2. Extended Output Characteristics
@ 25°C**



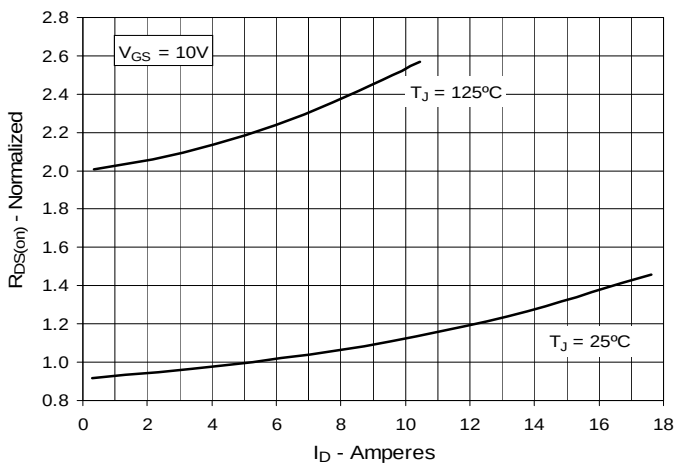
**Fig. 3. Output Characteristics
@ 125°C**



**Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 5A$ Value
vs. Junction Temperature**



**Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 5A$ Value
vs. Drain Current**



**Fig. 6. Maximum Drain Current vs.
Case Temperature**

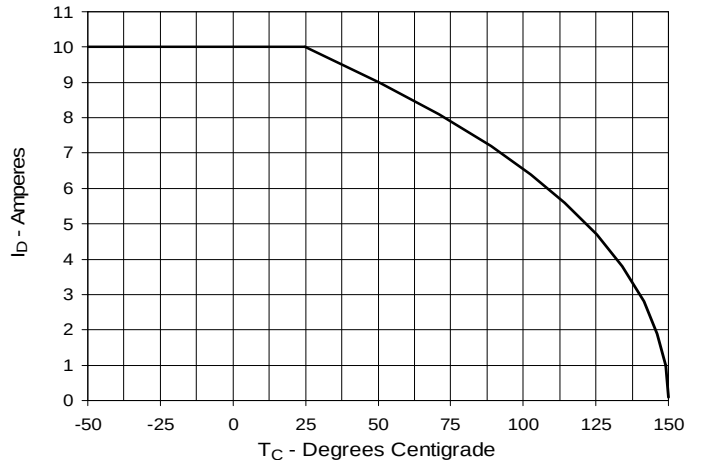


Fig. 7. Input Admittance

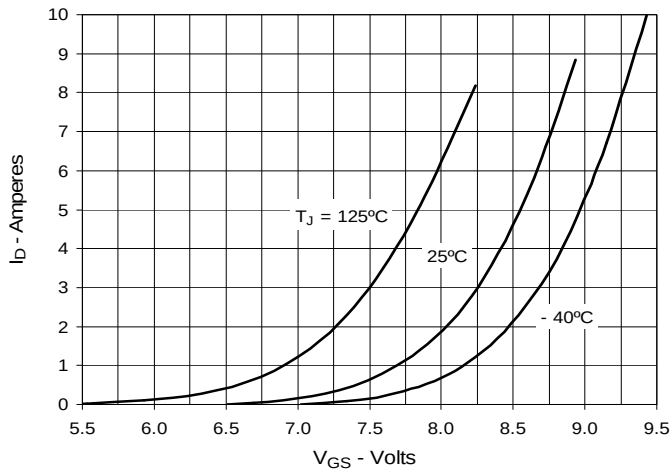


Fig. 8. Transconductance

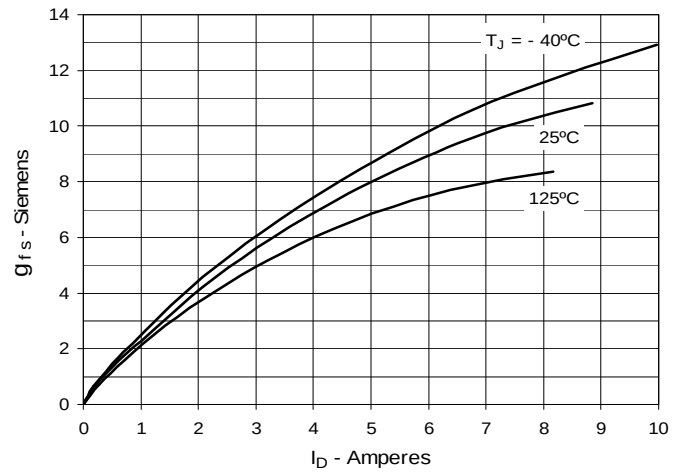


Fig. 9. Forward Voltage Drop of Intrinsic Diode

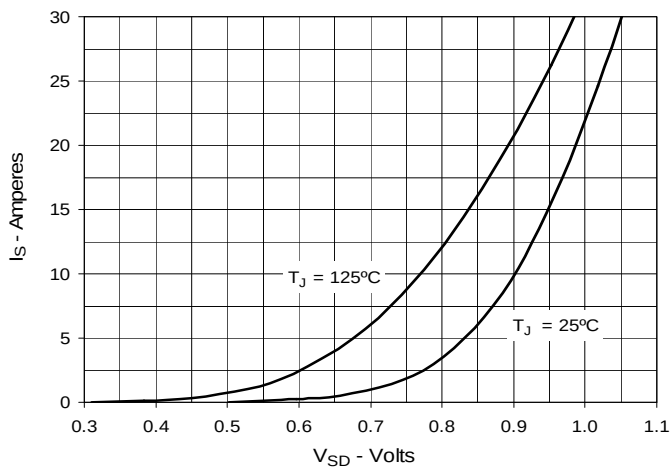


Fig. 10. Gate Charge

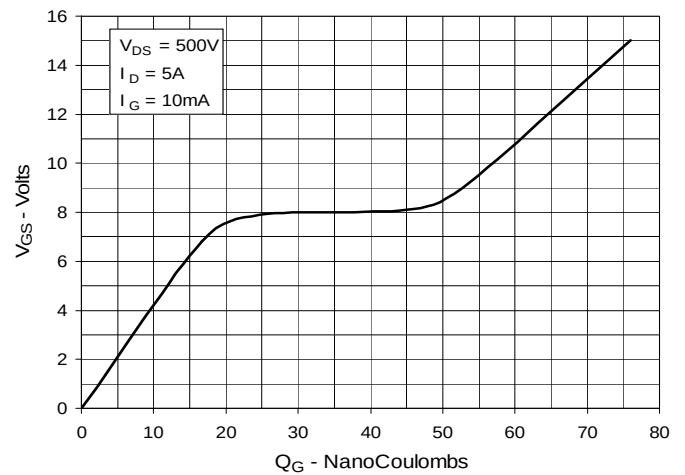


Fig. 11. Capacitance

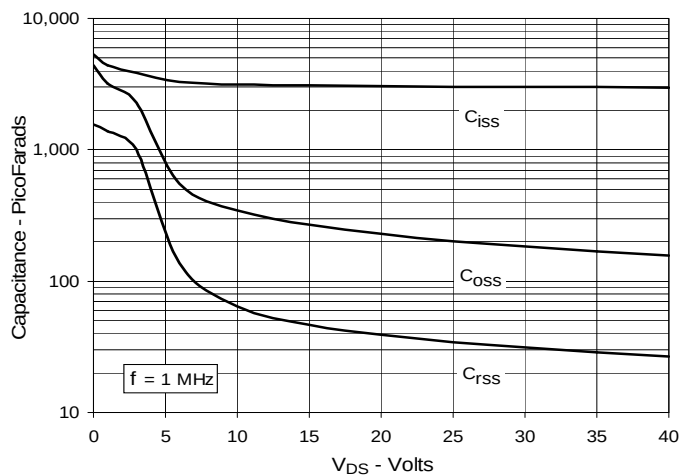


Fig. 12. Maximum Transient Thermal Impedance

